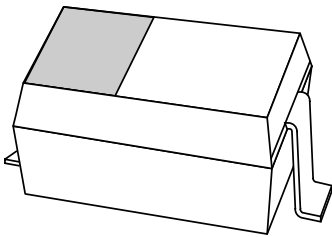


DATA SHEET



PMEG2010EA

Low V_F MEGA Schottky barrier diode

Product specification

2002 Dec 10

Low V_F MEGA Schottky barrier diode

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FEATURES

- Forward current: 1 A
- Reverse voltage: 20 V
- Ultra high-speed switching
- Very low forward voltage
- Very small plastic SMD package.

APPLICATIONS

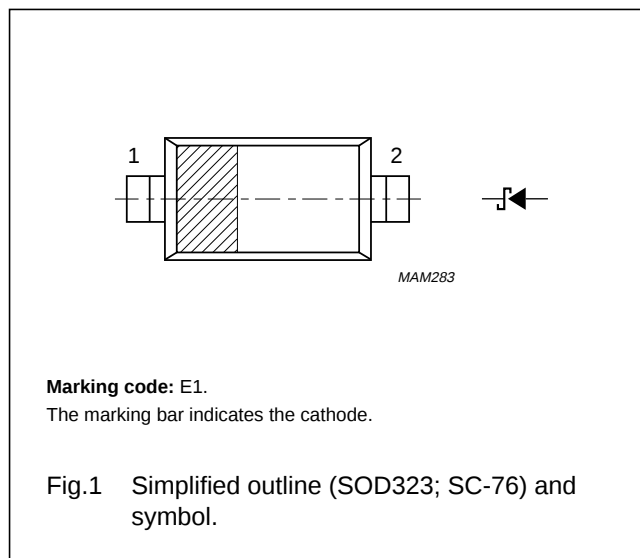
- Ultra high-speed switching
- Voltage clamping
- Protection circuits.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOD323 (SC-76) very small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	20	V
I_F	continuous forward current		–	1	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8.3$ ms half sinewave; JEDEC method	–	5	A
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	125	°C
T_{amb}	operating ambient temperature		–65	+125	°C

Low V_F MEGA Schottky barrier diode

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ELECTRICAL CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	continuous forward voltage	see Fig.2; note 1			
		$I_F = 10\text{ mA}$	240	270	mV
		$I_F = 100\text{ mA}$	300	350	mV
		$I_F = 1000\text{ mA}$	480	550	mV
I_R	continuous reverse current	see Fig.3; note 1			
		$V_R = 5\text{ V}$	5	10	μA
		$V_R = 8\text{ V}$	7	20	μA
		$V_R = 15\text{ V}$	10	50	μA
C_d	diode capacitance	$V_R = 5\text{ V}$; $f = 1\text{ MHz}$; see Fig.4	19	25	pF

Note

1. Pulsed test: $t_p = 300\text{ }\mu\text{s}$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	220	K/W
		note 2	180	K/W

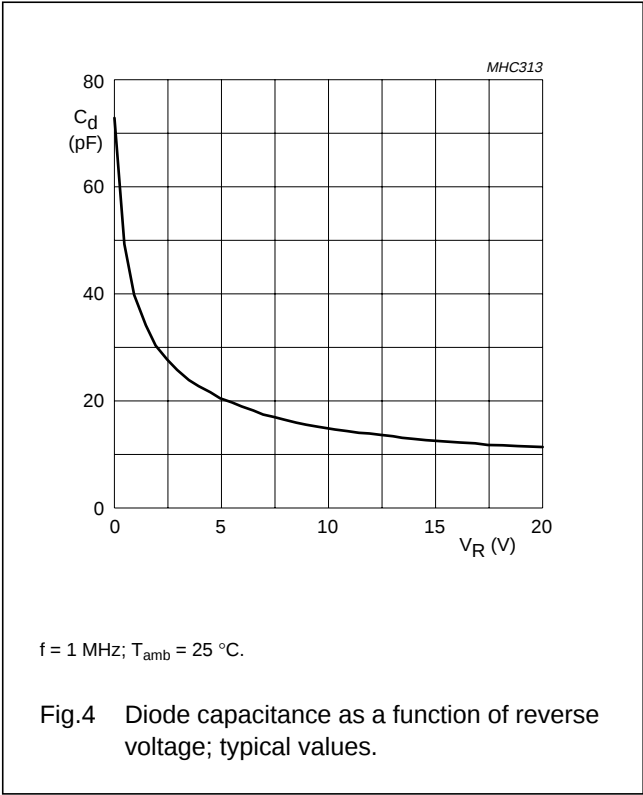
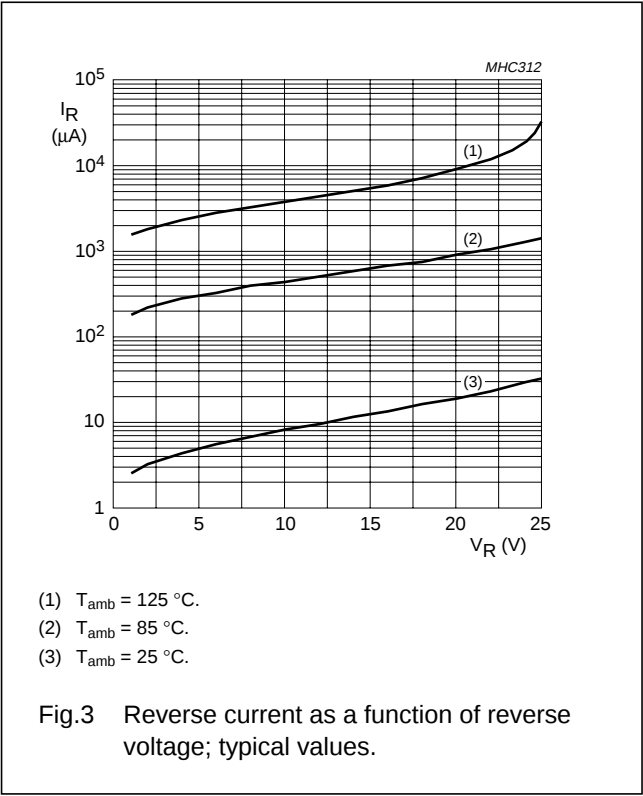
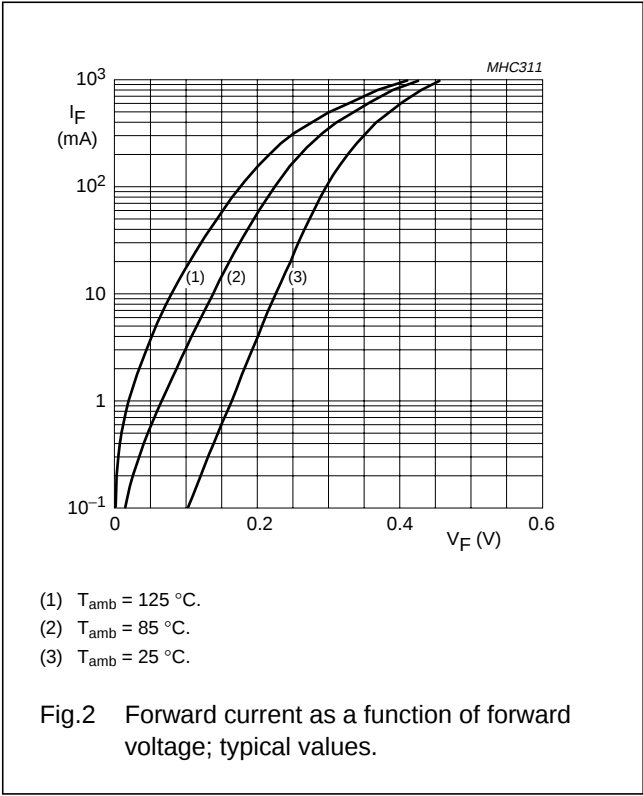
Notes

1. Device mounted on an FR4 printed-circuit board with Cu clad 10 x 10 mm.
2. Device mounted on an FR4 printed-circuit board with Cu clad 40 x 40 mm.

Low V_F MEGA Schottky barrier diode

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GRAPHICAL DATA



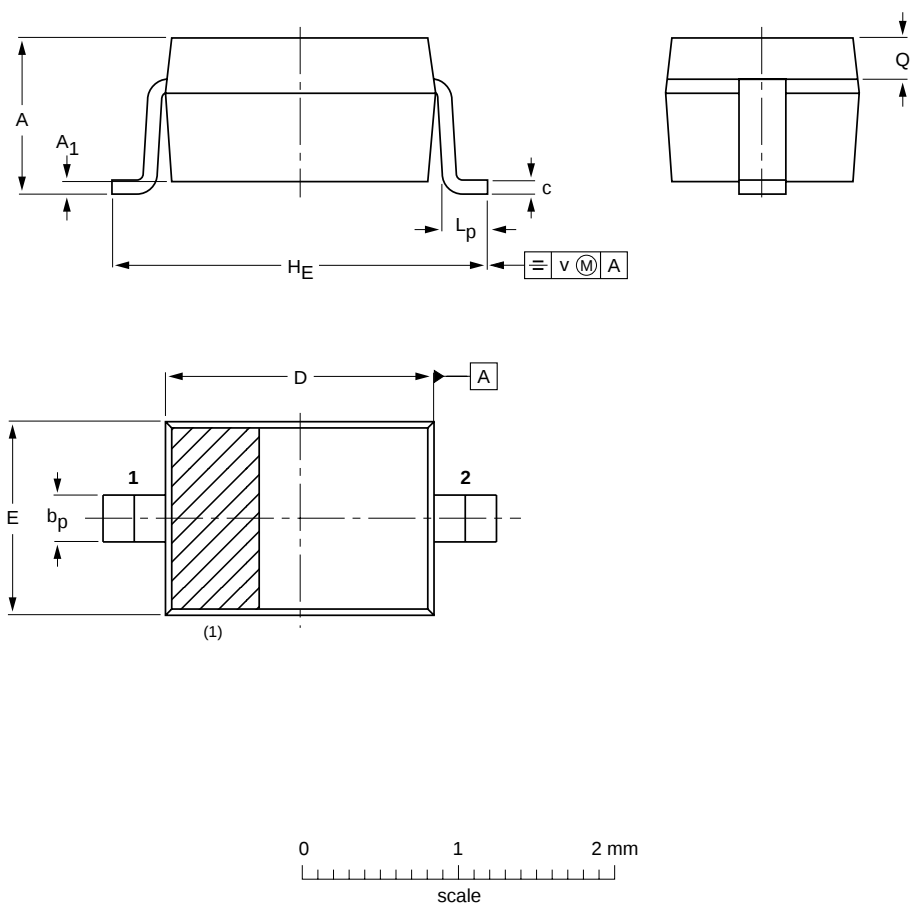
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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	H _E	L _p	Q	v
mm	1.1 0.8	+ 0.05 - 0.05	0.40 0.25	0.25 0.10	1.8 1.6	1.35 1.15	2.7 2.3	0.45 0.15	0.25 0.15	0.2

Note
1. The marking bar indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD323			SC-76			98-09-14 99-09-13

Low V_F MEGA Schottky barrier diode

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Notes

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Printed in The Netherlands

613514/01/pp8

Date of release: 2002 Dec 10

Document order number: 9397 750 10643

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